勝特力材料 886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw





INA110

Fast-Settling FET-Input INSTRUMENTATION AMPLIFIER

FEATURES

- LOW BIAS CURRENT: 50pA max
- FAST SETTLING: 4µs to 0.01%
- HIGH CMR: 106dB min; 90dB at 10kHz
- INTERNAL GAINS: 1, 10, 100, 200, 500
- VERY LOW GAIN DRIFT: 10 to 50ppm/°C
- LOW OFFSET DRIFT: 2µV/°C
- LOW COST
- PINOUT SIMILAR TO AD524 AND AD624

DESCRIPTION

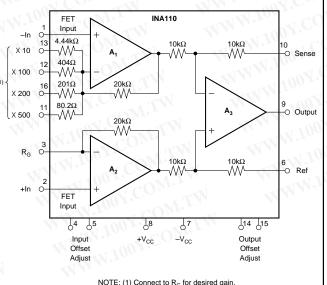
The INA110 is a versatile monolithic FET-input instrumentation amplifier. Its current-feedback circuit topology and laser trimmed input stage provide excellent dynamic performance and accuracy. The (n) INA110 settles in 4 μ s to 0.01%, making it ideal for high speed or multiplexed-input data acquisition systems.

Internal gain-set resistors are provided for gains of 1, 10, 100, 200, and 500V/V. Inputs are protected for differential and common-mode voltages up to $\pm V_{CC}$. Its very high input impedance and low input bias current make the INA110 ideal for applications requiring input filters or input protection circuitry.

The INA110 is available in 16-pin plastic and ceramic DIPs, and in the SOL-16 surface-mount package. Military, industrial and commercial temperature range grades are available.

APPLICATIONS

- MULTIPLEXED INPUT DATA ACQUISITION SYSTEM
- FAST DIFFERENTIAL PULSE AMPLIFIER
- HIGH SPEED GAIN BLOCK
- AMPLIFICATION OF HIGH IMPEDANCE SOURCES



International Airport Industrial Park

Mailing Address: PO Box 11400

Tucson, AZ 85734

Street Address: 6730 S. Tucson Blvd.

Tucson, AZ 85706
Tel: (520) 746-1111

Twx: 910-952-1111

Cable: BBRCORP

Telex: 066-6491

FAX: (520) 889-1510

Immediate Product Info: (800) 548-6132

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WWW.100Y.COM.TW WW.100X.COM.TW **SPECIFICATIONS**

NWW.1007.COM.TW por.com.mv At +25°C, $\pm V_{CC}$ = 15VDC, and R_L = 2k Ω , unless otherwise specified. WWW.100Y.COM.T 勝特力材料 886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787

		specified.			INA110KP, KU						
PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	A110BG, TYP	MAX	MIN	А110КР, ТҮР	MAX	UNITS
GAIN	WWW.			No.			NN		CONT	Wr.	
Range of Gain		1	0	800	*		*	*	100	*	V/V
Gain Equation ⁽¹⁾	WWW		N.O	177	G = 1 ·	+ [40k/(R _G		100	*	VT.	V/V
Gain Error, DC: G = 1		$\times 10^{\circ}$	0.002	0.04		*	0.02	100	*	*	%
G = 10	WW		0.01	0.1	N	0.005	0.05	100	*	*	%
G = 100		-x11	0.02	0.2		0.01	0.1	N.10	*	*	%
G = 200	Vu V	11.	0.04	0.4	W	0.02	0.2		*		%
G = 500			0.1	1		0.05	0.5	N.1	*	*	%
Gain Temp. Coefficient: G = 1	Tes In	V V.	±3	±20	N.	*	±10		*		ppm/°C
G = 10			±4	±20	1.1	±2	±10	-TN.		CON	ppm/°C
G = 100	The Mark		±6	±40		±3	±20				ppm/°C
G = 200	T. A. A.		±10	±60	N.1	±5	±30	-TN	100	0	ppm/°C
G = 500	- T	AT N	±25	±100	11-	±10	±50	IN Y			ppm/°C
Nonlinearity, DC: $G = 1$			±0.001	±0.01	M.	±0.0005	±0.005		1100		% of FS
G = 10			±0.002	±0.01	J.	±0.001	±0.005	N W	1		% of FS
G = 100	VT N		±0.004	±0.02	Mo	±0.002	±0.01		~ 10		% of FS
G = 200	NL.		±0.006	±0.02	U	±0.003	±0.01	WIX-	1	¢.C	% of FS
G = 500	NTN.	N	±0.01	±0.04		±0.005	±0.02	N.	*	00 * .	% of FS
OUTPUT). M		NN.	1	COr			-	N AL.		
Voltage, $R_L = 2k\Omega$	Over Temperature	±10	±12.7	1001	*	*		*	*	1007.	V
Current	Over Temperature	±5	±25		7 (* ()	*	N	* <1	*		mA
Short-Circuit Current	WT .		±25	1100	1.				*	1003	mA
Capacitive Load	Stability		5000	N	-1 C.	*	I		*		pF
INPUT OFFSET VOLTAGE ⁽²⁾	WT		N.Y.	110	37.	and a				AT 100	-0
Initial Offset: G, P	CONT		±(100 +	±(500 +	-1	±(50 +	±(250 +		*	*	μν
	WT VI		1000/G)	5000/G)	01.	600/G)	3000/G)		N. C	10	U
U .100	CON.			0000,00	_ <1	0.00,00,			+(200 +	±(1000 +	μν.Ο
	N.V. TV				1001	-	VT.		2000/G)	5000/G)	00.1
vs Temperature	CONT	≪1	±(2 +	±(5 +		±(1 +	±(2 +		*	1 2000,0)	μV/°C
	NY.V.	N	20/G)	100/G)	100	10/G)	50/G)			-	h003-
vs Supply	$V_{CC} = \pm 6V$ to $\pm 18V$		±(4 +	±(30 +	.100	±(2 +	±(10 +	s 1	*	*	μV/V
	00 _01.0 ±107	N I	60/G)	300/G)	110	30/G)	180/G)	14			L (100)
BIAS CURRENT	M. COM.	► 1			N					AT W	
Initial Bias Current	Each Input	WT	20	100	-11	10	50		*	*	
Initial Offset Current	Lacit input	· _	20	50	W. P	10	25		*	*	pA pA
Impedance: Differential	1001.00	VT.	2 5x10 ¹² 6		-1	100 *	20	2.11	*	N	Ω∥pF
Common-Mode	N.10° - COI	1.	2x10 ¹² 1		NV.	* <1	ICO _M		*	-	Ω pF
		T				1003		A TW			P'
VOLTAGE RANGE	V_{IN} Diff. = $0V^{(3)}$	Nr	×1	_	WINT				× .		W.V.,
Range, Linear Response		±10	±12			1100	¥.~		*		V
CMR with $1k\Omega$ Source Imbalance:		DY.			00	400				_	
G = 1	DC	70	90		80	100	11.0				dB
G = 10	DC	87	104		96	112	-1 C	O Ar			dB
G = 100	DC	100	110		106	116	101.				dB
G = 200	DC	100	110	ł	106	116	-1	10^{NL}			dB
G = 500	DC	100	110		106	116	Looy.		N N		dB
INPUT NOISE ⁽⁴⁾	W.Ivo		Nr.	-1		WIN	10	CON	-		
Voltage, f _O = 10kHz	WW The sol	N.V.	10	N		*	L OON		*		nV/√Hz
$f_B = 0.1Hz$ to 10Hz	1 N.100		1			*	1.100	- 00	*	1	μVp-p
Current, f _O = 10kHz	WWW.	\mathbf{V}	1.8			*	1	Y.V.	*	NN .	fA/√Hz
	L'ANT	N 2	-ON-				N.J.	10	DN	241	
Voltage, f _o = 10kHz	WW	No.	65	W		*	1	NY.V		CVV -	nV/√Hz
$f_B = 0.1$ Hz to 10Hz	1.1	00 -	8			*	W.W		0*1		μVp-p
-		Page 1		111			N . N . 	hox.			- <u>441 w</u>
		Voo ,	1.00	1.1			NN.	0.	*		
Small Signal: G = 1	–3dB		2.5	Vn.		*					MHz
G = 10		u 100	2.5	M.							MHz
G = 100	WIX	1.0	470	1	N	*			*		kHz
G = 200	N	x 10	240	hM.1	4.1	*			*		kHz
G = 500	Wize a	NN	100	0		*			*		kHz
Full Power	$V_{OUT} = \pm 10V,$		00 <u>7</u> .								
	G = 2 to 100	190	270		*	*			*	*	kHz
Slew Rate	G = 2 to 100	12	17		*	*			*	*	V/µs
Settling Time:											
0.1%, G = 1	V _O = 20V Step		4			*			*		μs
G = 10			2			*			*		μs
G = 100			3			*			*		μs
G = 200			5			*			*		μs
G = 500		1	11	1	1	*	1	1	*	1	μs



SPECIFICATIONS (CONT)

ELECTRICAL

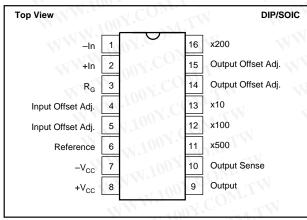
At +25°C, $\pm V_{CC}$ 15VDC, and R_L = 2K Ω , unless otherwise specified.

-OM-1	W.IV.	INA110AG		INA110BG, SG			INA110KP, KU				
PARAMETER	CONDITIONS	MIN	TYP	МАХ	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
DYNAMIC RESPONSE (CONT)	You WV		WT .		NV.		00Y.		TN		
Settling Time:	100 -		1.1			ATV.	0	CON			
0.01%,G = 1	V _o = 20V Step		5	12.5	N/	*	*		*		μs
G = 10	N 100	0	3	7.5		*	*		*		μs
G = 100	WWW.	\mathbf{V}	4	7.5	1	*	. *		*	N	μs
G = 200	N 101		7	12.5		*	*		*		μs
G = 500	ALVN.	V C	16	25		*	*	$\sqrt{1}$	*		μs
Recovery ⁽⁵⁾	50% Overdrive	01	11.			*	N.10		*		μs
POWER SUPPLY	NV WIL	- N.		W		NV.		1.		N	
Rated Voltage			±15			*	N.		*	-1	V
Voltage Range		±6	CO	±18	*		*	*		*	V
Quiescent Current	$V_0 = 0V$	100 .	±3	±4.5		*	*	100 -	(\mathbf{A})	*	mA
TEMPERATURE RANGE	N.V.	- 100	1.0	TI	N			1003		1.1	
Specification: A, B, K		-25		+85	*		*	0	$_{1}CO$	+70	°C
S			N		-55		+125	1100	1.	N 3	°C
Operation		-55	. C	+125	*		*	-25	-1 C	+85	°C
Storage	N W	-65		+150	*		*	-40	N	+85	°C
θ_{JA}		. IN	100	-01-	1 m	*		N.10	*	ON.	°C/W
					N To						

* Same as INA110AG.

NOTES: (1) Gains other than 1, 10, 100, 200, and 500 can be set by adding an external resistor, R_G, between pin 3 and pins 11, 12 and 16. Gain accuracy is a function of R_G and the internal resistors which have a $\pm 20\%$ tolerance with 20ppm/°C drift. (2) Adjustable to zero. (3) For differential input voltage other than zero, see Typical Performance Curves. (4) V_{NOISE RTI} = $\sqrt{V_N^2}_{|NPUT} + (V_{N OUTPUT}/Gain)^2$. (5) Time required for output to return from saturation to linear operation following the removal of an input overdrive voltage.





ORDERING INFORMATION

MODEL	PACKAGE	TEMPERATURE RANGE
INA110AG	16-Pin Ceramic DIP	-25°C to +85°C
INA110BG	16-Pin Ceramic DIP	-25°C to +85°C
INA110SG	16-Pin Ceramic DIP	−55°C to +125°C
INA110KP	16-Pin Plastic DIP	0°C to +70°C
INA110KU	SOL-16 SOIC	0°C to +70°C

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±18V
Input Voltage Range	±V _{CC}
Operating Temperature Range: G	55°C to +125°C
P, U	–25°C to +85°C
Storage Temperature Range: G	–65°C to +150°C
P, U	40°C to +85°C
Lead Temperature (soldering, 10s): G, P	+300°C
(soldering, 3s): U	+260°C
Output Short Circuit Duration	. Continuous to Common

PACKAGE INFORMATION

MODEL	PACKAGE	PACKAGE DRAWING NUMBER ⁽¹⁾
INA110AG	16-Pin Ceramic DIP	109
INA110BG	16-Pin Ceramic DIP	109
INA110SG	16-Pin Ceramic DIP	109
INA110KP	16-Pin Plastic DIP	180
INA110KU	SOL-16 SOIC	211

NOTE: (1) For detailed drawing and dimension table, please see end of data sheet, or Appendix D of Burr-Brown IC Data Book.

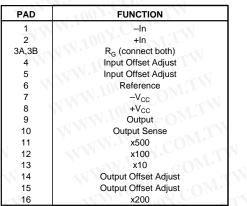
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DICE INFORMATION

 Image: Second second

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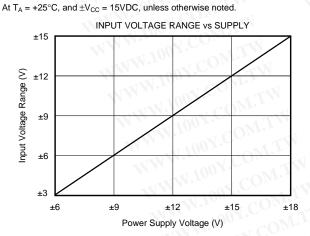
Pads 3A and 3B must be connected.

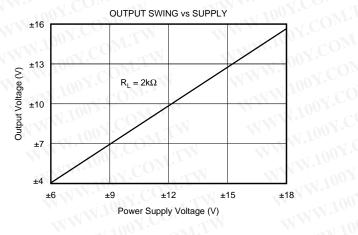
Substrate Bias: Internally connected to -V_{CC} power supply.

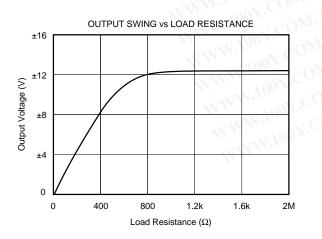
MECHANICAL INFORMATION

WT	MILS (0.001")	MILLIMETERS
Die Size	139 x 89 ±5	3.53 x 2.26 ±0.13
Die Thickness	20 ±3	0.51 ±0.08
Min. Pad Size	4 x 4	0.10 x 0.10
Backing		Gold

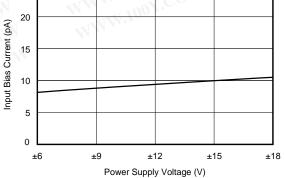
TYPICAL PERFORMANCE CURVES







BIAS CURRENT vs SUPPLY



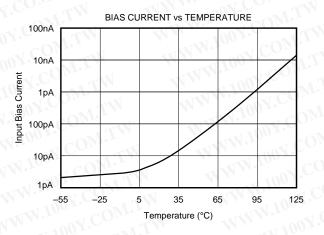


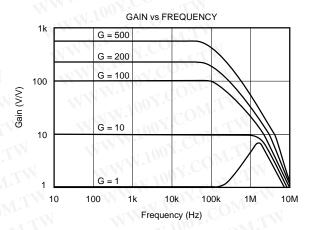
25

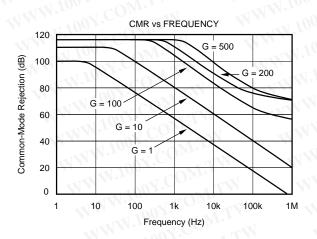
TYPICAL PERFORMANCE CURVES (CONT)

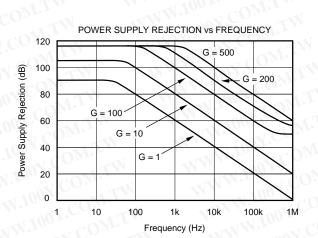
 T_{A} = +25°C, $\pm V_{CC}$ = 15VDC, unless otherwise noted.

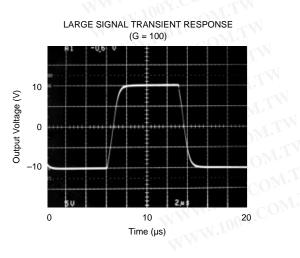
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SMALL SIGNAL TRANSIENT RESPONSE (G = 100)

10

Time (µs)

INA110



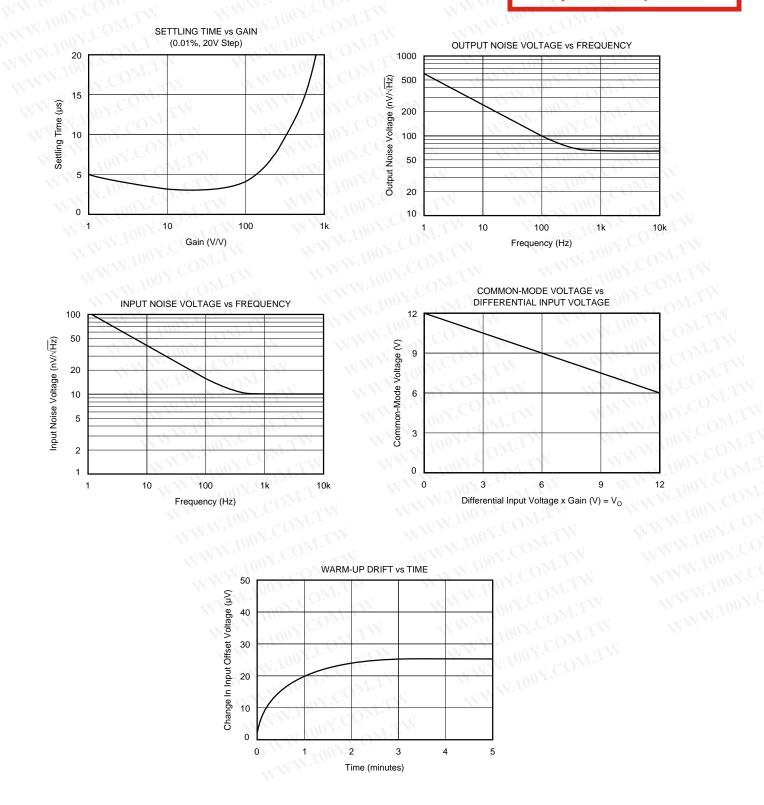
20

0

TYPICAL PERFORMANCE CURVES (CONT)

 $T_A = +25^{\circ}C, \pm V_{CC} = 15VDC$, unless otherwise noted.

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DISCUSSION OF PERFORMANCE

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A simplified diagram of the INA110 is shown on the first page. The design consists of the classical three operational amplifier configuration using current-feedback type op amps with precision FET buffers on the input. The result is an instrumentation amplifier with premium performance not normally found in integrated circuits.

The input section (A₁ and A₂) incorporates high performance, low bias current, and low drift amplifier circuitry. The amplifiers are connected in the noninverting configuration to provide high input impedance ($10^{12}\Omega$). Laser-trimming is used to achieve low offset voltage. Input cascoding assures low bias current and high CMR. Thin-film resistors on the integrated circuit provide excellent gain accuracy and temperature stability.

The output section (A₃) is connected in a unity-gain difference amplifier configuration. Precision matching of the four $10k\Omega$ resistors, especially over temperature and time, assures high common-mode rejection.

BASIC POWER SUPPLY AND SIGNAL CONNECTIONS

Figure 1 shows the proper connections for power supply and signal. Supplies should be decoupled with 1μ F tantalum capacitors as close to the amplifier as possible. To avoid gain and CMR errors introduced by the external circuit, connect grounds as indicated, being sure to minimize ground resistance. Resistance in series with the reference (pin 6) will degrade CMR. To maintain stability, avoid capacitance from the output to the gain set, offset adjust, and input pins.

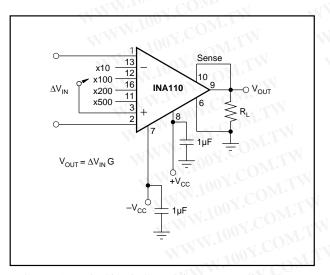


FIGURE 1. Basic Circuit Connection.

OFFSET ADJUSTMENT

Figure 2 shows the offset adjustment circuit for the INA110. Both the offset of the input stage and output stage can be adjusted separately. Notice that the offset referred to the INA110's input (RTI) is the offset of the input stage plus the offset of the output stage divided by the gain of the input stage. This allows specification of offset independent of gain.

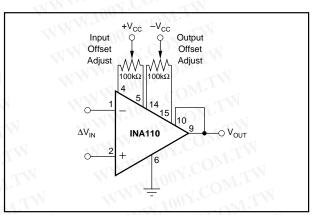


FIGURE 2. Offset Adjustment Circuit.

For systems using computer autozeroing techniques, neither offset nor offset drift are of concern. In many other applications, the factory-trimmed offset gives excellent results. When greater accuracy is desired, one adjustment is usually sufficient. In high gains (>100) adjust only the input offset, and in low gains the output offset. For higher precision in all gains, both can be adjusted by first selecting high gain and adjusting input offset and then low gain and adjusting output offset. The offset adjustment will, however, add to the drift by approximately $0.33\mu V/^{\circ}C$ per $100\mu V$ of input offset voltage that is adjusted. Therefore, care should be taken when considering use of adjustment.

Output offsetting can be accomplished as shown in Figure 3 by applying a voltage to the reference (pin 6) through a buffer. This limits the resistance in series with pin 6 to minimize CMR error. Be certain to keep this resistance low. Note that the offset error can be adjusted at this reference point with no appreciable degradation in offset drift.

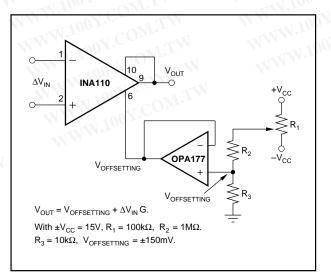


FIGURE 3. Output Offsetting.



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GAIN SELECTION

Gain selection is accomplished by connecting the appropriate pins together on the INA110. Table I shows possible gains from the internal resistors. Keep the connections as short as possible to maintain accuracy.

GAIN	CONNECT PIN 3 TO PIN	GAIN ACCURACY (%)	GAIN DRIFT (ppm/°C)
The follow	ing gains have guaran	teed accuracy:	W.L
1	none	0.02	10
10	13	0.05	10
100	12	0.1	20
200	16	0.2	30
500	11	0.5	50
The follow	ing gains have typical	accuracy as shown:	WWW.
300	12, 16	0.25	10
600	11, 12	0.25	40
700	11, 16	2	40
800	11, 12, 16	2	80

TABLE I. Internal Gain Connections.

Gains other than 1, 10, 100, 200, and 500 can be set by adding an external resistor, R_G , between pin 3 and pins 12, 16, and 11. Gain accuracy is a function of R_G and the internal resistors which have a $\pm 20\%$ tolerance with 20ppm/°C drift. The equation for choosing R_G is shown below.

$$R_{\rm G} = \frac{40k}{G-1} - 50\Omega$$

Gain can also be changed in the output stage by adding resistance to the feedback loop shown in Figure 4. This is useful for increasing the total gain or reducing the input stage gain to prevent saturation of input amplifiers.

The output gain can be changed as shown in Table II. Matching of R_1 and R_3 is required to maintain high CMR. R_2 sets the gain with no effect on CMR.

OUTPUT STAGE GAIN	R ₁ AND R ₃	R ₂
2	1.2kΩ	2.74kΩ
5	1kΩ	511Ω
10	1.5kΩ	340Ω

TABLE II. Output Stage Gain Control.

COMMON-MODE INPUT RANGE

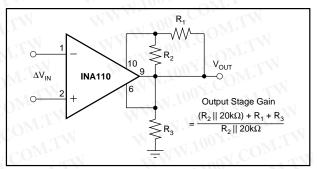
It is important not to exceed the input amplifiers' dynamic range (see Typical Performance Curves). The differential input signal and its associated common-mode voltage should not cause the output of A_1 and A_2 (input amplifiers) to exceed approximately ±10V with ±15V supplies or nonlinear operation will result. Such large common-mode voltages, when the INA110 is in high gain, can cause saturation of the input stage even though the differential input is very small. This can be avoided by reducing the input stage gain and increasing the output stage gain with an H pad attenuator (see Figure 4).

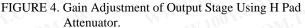
OUTPUT SENSE

An output sense has been provided to allow greater accuracy in connecting the load. By attaching this feedback point to the load at the load site, IR drops due to load currents that



are eliminated since they are inside the feedback loop. Proper connection is shown in Figure 1. When more current is to be supplied, a power booster can be placed within the feedback loop as shown in Figure 5. Buffer errors are minimized by the loop gain of the output amplifier.





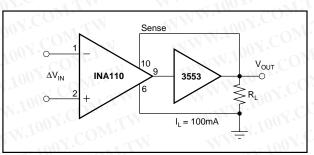


FIGURE 5. Current Boosting the Output.

LOW BIAS CURRENT OF FET INPUT ELIMINATES DC ERRORS

Because the INA110 has FET inputs, bias currents drawn through input source resistors have a negligible effect on DC accuracy. The picoamp levels produce no more than microvolts through megohm sources. Thus, input filtering and input series protection are readily achievable.

A return path for the input bias currents must always be provided to prevent charging of stray capacitance. Otherwise, the output can wander and saturate. A $1M\Omega$ to $10M\Omega$ resistor from the input to common will return floating sources such as transformers, thermocouples, and AC-coupled inputs (see Applications section).

DYNAMIC PERFORMANCE

The INA110 is a fast-settling FET input instrumentation amplifier. Therefore, careful attention to minimize stray capacitance is necessary to achieve specified performance. High source resistance will interact with input capacitance to reduce the overall bandwidth. Also, to maintain stability, avoid capacitance from the output to the gain set, offset adjust, and input pins.

Applications with balanced-source impedance will provide the best performance. In some applications, mismatched source impedances may be required. If the impedance in the negative input exceeds that in the positive input, stray capacitance from the output will create a net negative feedback and improve the circuit stability. If the impedance in the positive input is greater, the feedback due to stray capacitance will be positive and instability may result. The degree of positive feedback depends upon source impedance imbalance, operating gain, and board layout. The addition of a small bypass capacitor of 5pF to 50pF directly between the inputs of the IA will generally eliminate any positive feedback. CMR errors due to the input impedance mismatch will also be reduced by the capacitor.

The INA110 is designed for fast settling with easy gain selection. It has especially excellent settling in high gain. It can also be used in fast-settling unity-gain applications. As with all such amplifiers, the INA110 does exhibit significant gain peaking when set to a gain of 1. It is, however, unconditionally stable. The gain peaking can be cancelled by band-limiting the negative input to 400kHz with a simple external RC circuit for applications requiring flat response. CMR is not affected by the addition of the 400kHz RC in a gain of 1.

Another distinct advantage of the INA110 is the high frequency CMR response. High frequency noise and sharp common-mode transients will be rejected. To preserve AC CMR, be sure to minimize stray capacitance on the input lines. Matching the RCs in the two inputs will help to maintain high AC CMR.

APPLICATIONS

In addition to general purpose uses, the INA110 is designed to accurately handle two important and demanding applications: (1) inputs with high source impedances such as capacitance/crystal/photodetector sensors and low-pass filters and series-input protection devices, and (2) rapidscanning data acquisition systems requiring fast settling time. Because the user has access to the output sense, current sources can also be constructed using a minimum of external components. Figures 6 through 19 show application circuits.

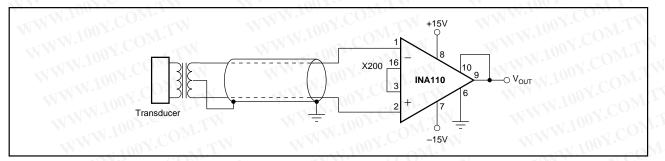


FIGURE 6. Transformer-Coupled Amplifier.

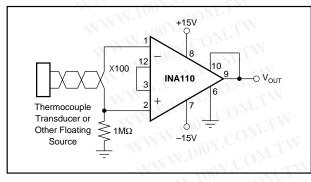


FIGURE 7. Floating Source Instrumentation Amplifier.



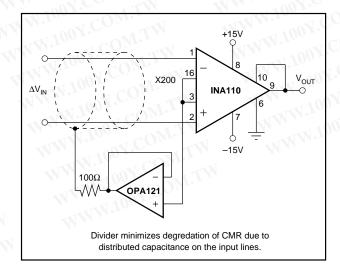
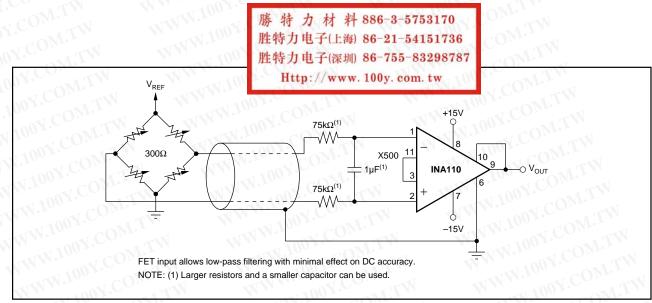
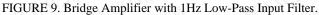


FIGURE 8. Instrumentation Amplifier with Shield Driver.

INA110







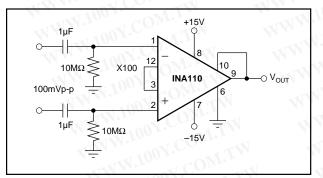


FIGURE 10. AC-Coupled Differential Amplifier for Frequencies Greater Than 0.016Hz.

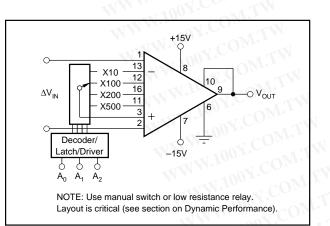


FIGURE 11. Programmable-Gain Instrumentation Amplifier (Precision Noninverting or Inverting Buffer with Gain). F

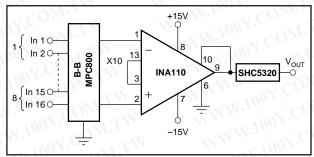
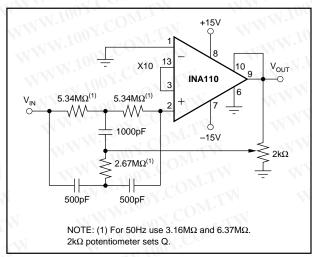
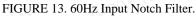
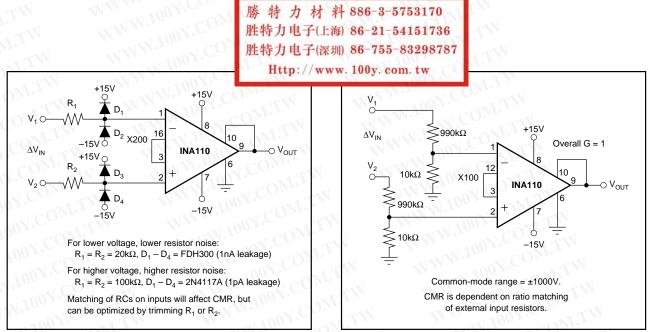


FIGURE 12. Rapid-Scanning-Rate Data Acquisition Channel with 5µs Settling to 0.01%.









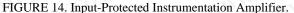


FIGURE 15. High Common-Mode Voltage Differential Amplifier.

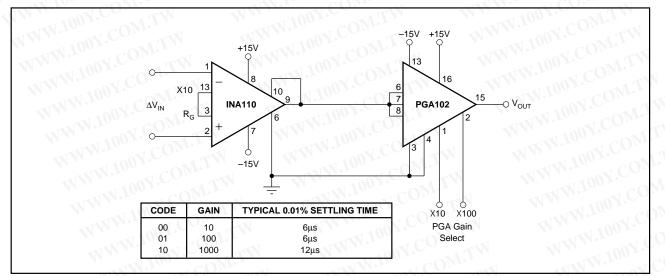


FIGURE 16. Digitally-Controlled Fast-Settling Programmable Gain Instrumentation Amplifier.

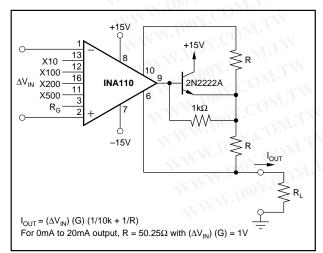


FIGURE 17. Differential Input FET Buffered Current Source.

